

Small signal switching Diodes

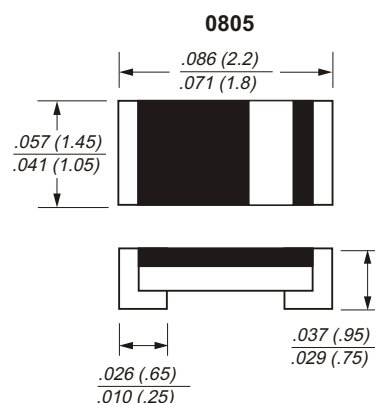
Foward Power Dissipation 200mW

FEATURES

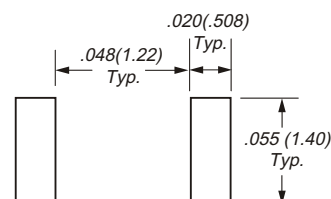
- Silicon epitaxial planar diode
SMD chip pattern, available in various dimension included 1206
- Fast switching diode.

MECHANICAL DATA

- Case : 0805
- Polarity : Color band denotes cathode
- Weight : 0.006 grams



Mounting Pad Layout



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

PARAMETER at Tamb=25	SYMBOL	Value	UNIT
Repetitive Peak Reverse Voltage	VRRM	100	V
Average forward rectified current sin half wave rectification with resistive load	IF(AV)	150	mA
Repetitive Peak Forward Current	IFRM	300	mA
Non-Repetitive Surge Forward Current @t<1s @t< 8.3ms	IFSM	500 1000	mA
Forward Voltage @10mA @100mA	VF	1.0 1.25	V
Leakage Current @20V @75V	IR	0.025 5.0	uA
Forward Power Dissipation Power derating about 25	Ptot	200 1.6	mW mW/
Capacitance @Vr=0V, f=1MHz	Ctot	4	pF
Reverse Recovery Time @IF=IR=10mA, RL=100	Trr	4	nS
Typical Thermal Resistance	R JA	375	/W
Operating Temperature Range	TJ	-55 to +150	
Storage Temperature Range	TSTG	-55 to +150	

TYPICAL CHARACTERISTICS

Figure 1. Forward Characteristic

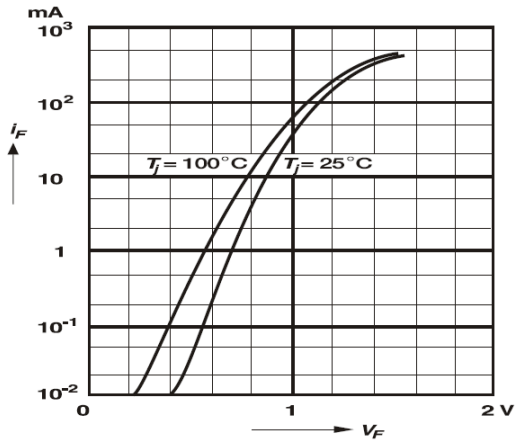


Figure 2. Power De-rating

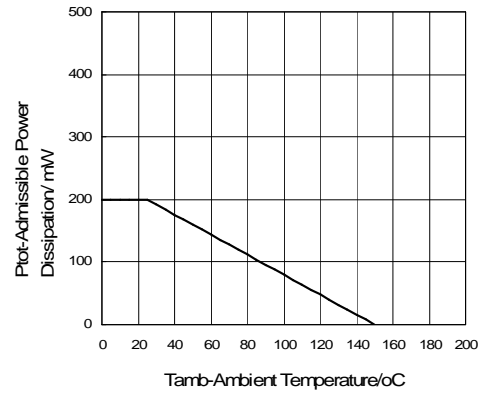


Figure 3. Forward Current De-rating

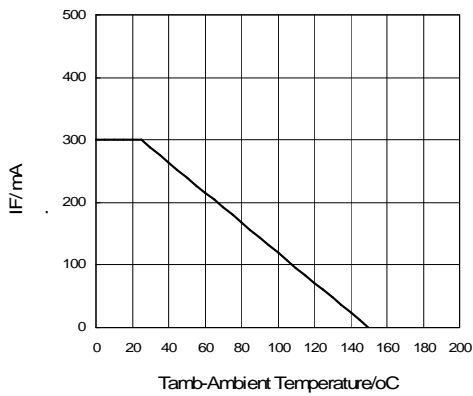


Figure 4. Reverse Voltage De-rating

